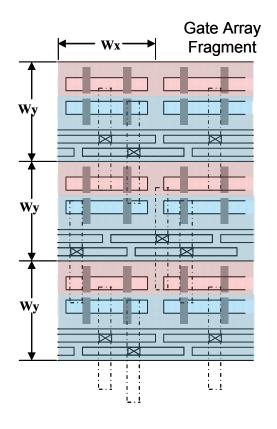
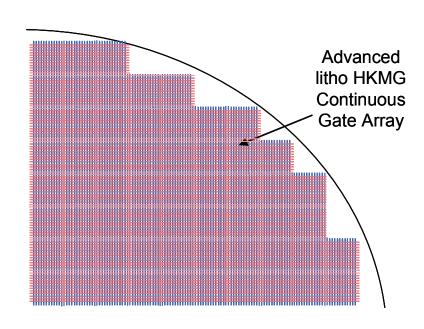


# Technology Breakthrough

## **Three-Dimensional Gate Array**





### **Technology:**

- Dense High Performance HKMG Gate Array with continuous N/P strips
- Layer Transfer with Ion Cut for 3D stacking
- Gate Replacement after Ion Cut
- Alignment error guaranteed smaller than Wx and Wy independent of Layer Transfer
- Multiple stacking for ultra dense arrays
- Mix of GA and Memory wafers in stack
- Unidirectional layout
- Continuous Array style of wafer patterning
- Etching scribe lines per application demand

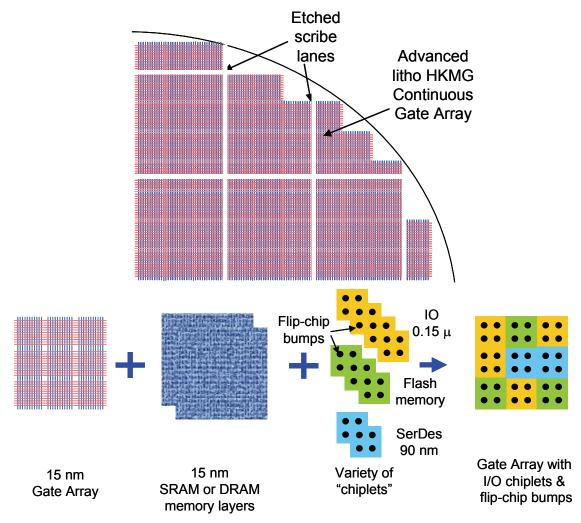
#### **Benefits:**

- Very high density Gate Array terrain
- Easy patterning with unidirectional layout
- Continuous Array allows flexible dicing for variable-sized chips
- 3D stacking allows flexible ratio between memory and logic
- 3D stacking allows ultra-high device density
- Single mask set for a complete range of Gate Arrays



# Technology Breakthrough

### **Inexpensive Arbitrary-sized Gate Array Manufacturing**



### **Chip-on-Wafer I/O Chiplet Assembly**

### **Technology:**

- Wafer-scale Continuous Array with custom-etched scribe lines
- Chiplets with I/O, analog functions, etc.
- Chiplets contain flip-chip bumping
- TSV or microbump-based Wafer-on-Wafer and Chip-on-Wafer 3D stacking

#### **Benefits:**

- Arbitrary-sized Gate Array
- Flexible I/O and analog function configuration
- Possible re-use of older prequalified silicon I/O together with most advanced logic technology
- Gate Array family no longer needs costly multiple mask sets